

SILICON NPN TRIPLE DIFFUSED TYPE
(DARLINGTON POWER MODULE)

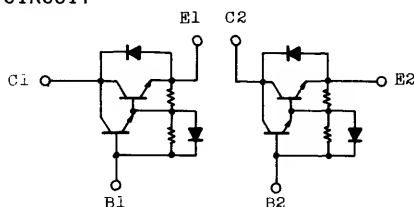
MG100H2DL1

HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

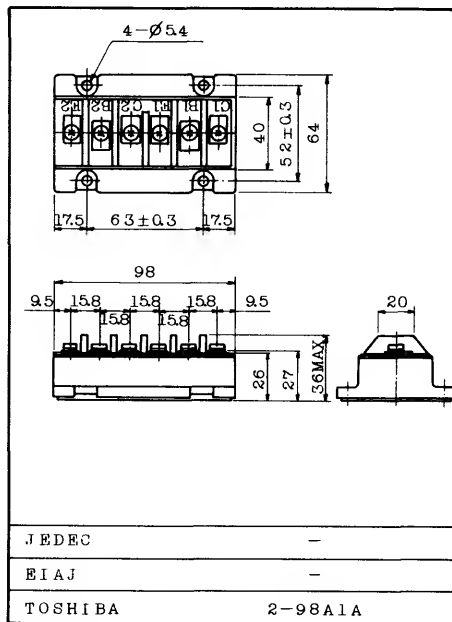
FEATURES:

- . The Collector is Isolated from Case.
- . With Built-in Free Wheeling Diode
- . High DC Current Gain : $h_{FE}=80(\text{Min.})(I_C=100A)$
- . Low Saturation Voltage : $V_{CE(sat)}=2V(\text{Max.})(I_C=100A)$
- . High Speed : $t_f=4\mu s(\text{Max.})(I_C=100A)$

EQUIVALENT CIRCUIT



Unit in mm



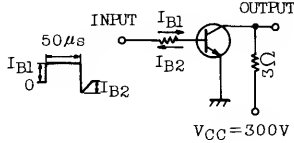
Weight :

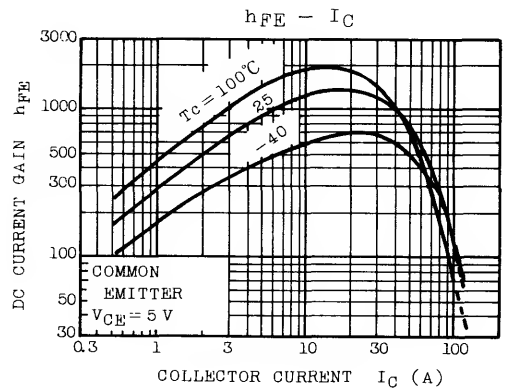
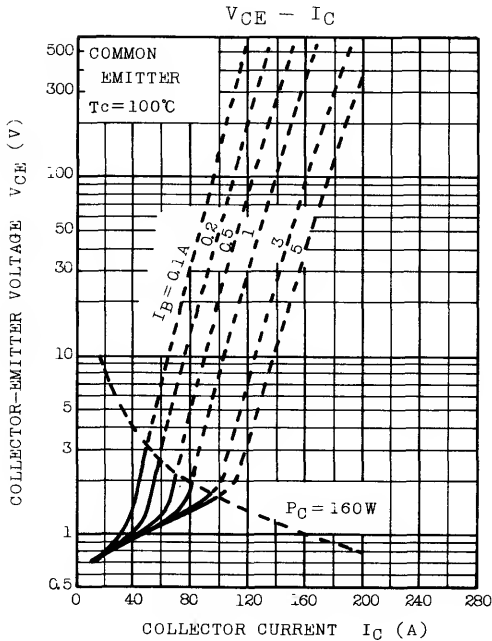
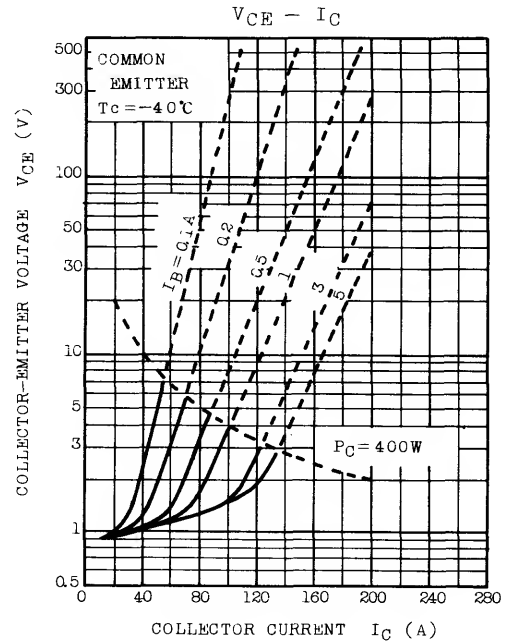
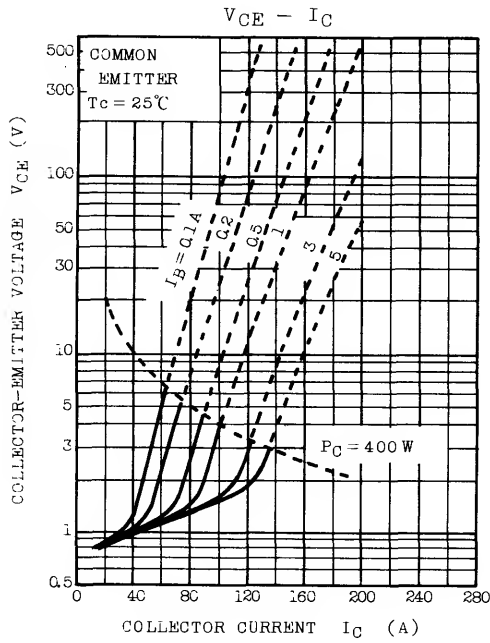
MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		$V_{CEO(SUS)}$	550	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current	DC	I_C	100	A
	1ms	I_{CP}	200	
	DC	$-I_C$	100	
Base Current		I_B	5	A
Collector Power Dissipation ($T_c=25^{\circ}C$)		P_C	400	W
Junction Temperature		T_j	150	$^{\circ}C$
Storage Temperature Range		T_{stg}	-40~125	$^{\circ}C$
Isolation Voltage		V_{Iso1}	2000(AC 1 Minute)	V
Screw Torque			30	kg·cm

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ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} =600V, I _E =0	-	-	2.0	mA
Emitter Cut-off Current		IEBO	VEB=6V, I _C =0	-	-	200	mA
Collector-Emitter Sustaining Voltage		V _{CEO} (SUS)	I _C =0.5A, L=40mH	550	-	-	V
DC Current Gain		h _{FE}	V _{CE} =5V, I _C =100A	80	-	-	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C =100A, I _B =3A	-	-	2.0	V
Base-Emitter Saturation Voltage		V _{BE} (sat)		-	-	2.7	V
Emitter-Collector Voltage		V _{ECO}	I _E =100A, I _B =0	-	-	1.5	V
Reverse Recovery Time		t _{rr}	-I _C =100A, V _{EB} =3V V _{CE} =300V	-	-	2.0	μs
Collector Output Capacitance		C _{ob}	V _{CB} =50V, I _E =0 f=1MHz	-	800	-	pF
Switching Time	Turn-on Time	t _{on}	 INPUT I_{B1} 50 μs I_{B1} 0 I_{B2} OUTPUT C_C V_{CC}=300V	-	-	2.0	μs
	Storage Time	t _{stg}		-	-	12	
	Fall Time	t _f		-	-	4.0	
Thermal Resistance (Junction to Case)		R _{th(j-c)}	Transistor	-	-	0.31	°C/W
			Diode	-	-	1.3	



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